

## Driver Transistors PNP Silicon

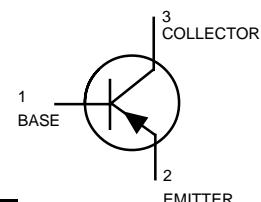
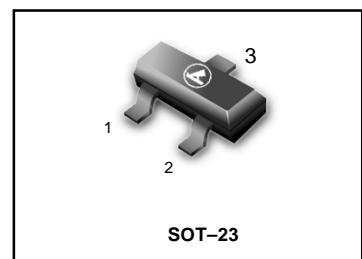
### ● FEATURES

- 1) We declare that the material of product compliant with RoHS requirements and Halogen Free.
- 2) S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

### ● DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LMBTA56LT1G	2GM	3000/Tape&Reel
LMBTA56LT3G	2GM	10000/Tape&Reel

**LMBTA56LT1G  
S-LMBTA56LT1G**



### ● MAXIMUM RATINGS(Ta = 25°C)

Parameter	Symbol	Limits	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	-80	Vdc
Collector-Base Voltage	V <sub>CBO</sub>	-80	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	-4.0	Vdc
Collector Current — Continuous	I <sub>c</sub>	-500	mAdc

### ● THERMAL CHARACTERISTICS

Parameter	Symbol	Limits	Unit
Total Power Dissipation FR-5 Board,(Note 1.)@Ta = 25°C	P <sub>D</sub>	225	mW
Derate above 25°C		1.8	°C/W
Thermal Resistance – Junction-to-Ambient	R <sub>θJA</sub>	556	°C/W
Total Power Dissipation Alumina Substrate,(Note 2.)@Ta = 25°C	P <sub>D</sub>	300	mW
Derate above 25°C		2.4	°C/W
Thermal Resistance, Junction-to-Ambient	R <sub>θJA</sub>	417	°C/W
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

1. FR-5 = 1.0 x 0.75 x 0.062 in.

2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

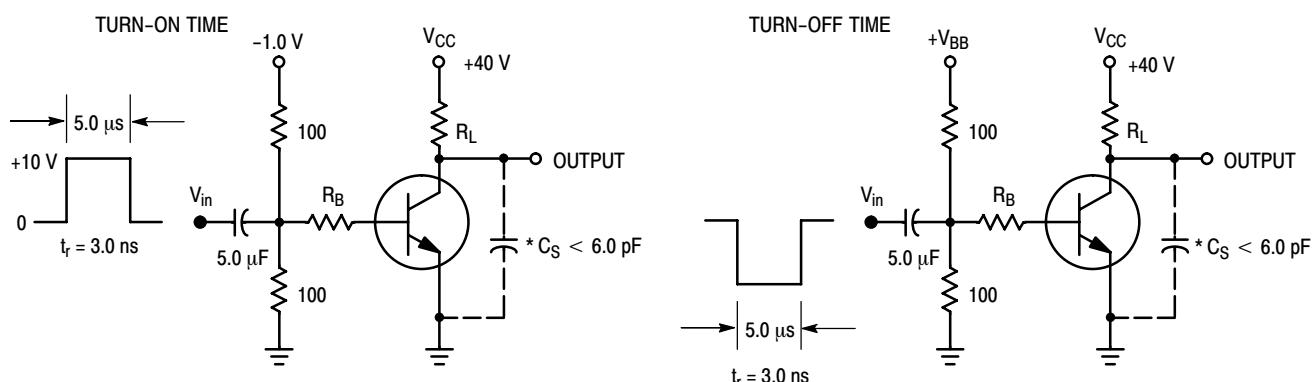
## LMBTA56LT1G,S-LMBTA56LT1G

●ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ C$ )

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Collector-Emitter Breakdown Voltage(Note 3) ( $I_c = -1 \text{ mA}_\text{dc}$ , $I_B = 0$ )	$V_{BR}(\text{CEO})$	-80	—	—	V
Emitter-Base Breakdown Voltage ( $I_E = -100 \mu\text{A}_\text{dc}$ , $I_C = 0$ )	$V_{BR}(\text{EBO})$	-4	—	—	V
Collector Cutoff Current ( $V_{CE} = -60 \text{ V}_\text{dc}$ , $I_E = 0$ )	$I_{CES}$	—	—	-0.1	$\mu\text{A}$
Collector Cutoff Current ( $V_{CB} = -80 \text{ V}_\text{dc}$ , $I_E = 0$ )	$I_{CBO}$	—	—	-0.1	$\mu\text{A}$
DC Current Gain ( $I_C = -10 \text{ mA}_\text{dc}$ , $V_{CE} = -1 \text{ V}_\text{dc}$ ) ( $I_C = -100 \text{ mA}_\text{dc}$ , $V_{CE} = -1 \text{ V}_\text{dc}$ )	$h_{FE}$	100 100	— —	— —	
Collector-Emitter Saturation Voltage ( $I_C = -100 \text{ mA}_\text{dc}$ , $I_B = -10 \text{ mA}_\text{dc}$ )	$V_{CE(\text{sat})}$	—	—	-0.25	V
Base-Emitter On Voltage ( $I_C = -100 \text{ mA}_\text{dc}$ , $V_{CE} = -1 \text{ mA}_\text{dc}$ )	$V_{BE(\text{on})}$	—	—	-1.20	V
Current-Gain — Bandwidth Product(Note 4.) ( $I_C = -100 \text{ mA}_\text{dc}$ , $V_{CE} = -1 \text{ V}_\text{dc}$ , $f = 100 \text{ MHz}$ )	$f_T$	50	—	—	MHz

3. Pulse Test: Pulse Width  $\leq 300 \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

4.  $f_T$  is defined as the frequency at which  $|h_{fe}|$  extrapolates to unity.



\*Total Shunt Capacitance of Test Jig and Connectors For PNP Test Circuits, Reverse All Voltage Polarities

Fig. 1 Switching Time Test Circuits

## **LMBTA56LT1G,S-LMBTA56LT1G**

### **ELRCTRICAL CHARACTERISTICS CURVES**

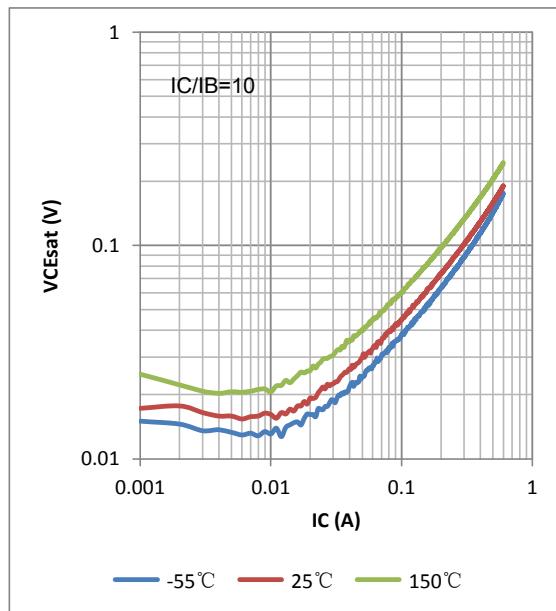
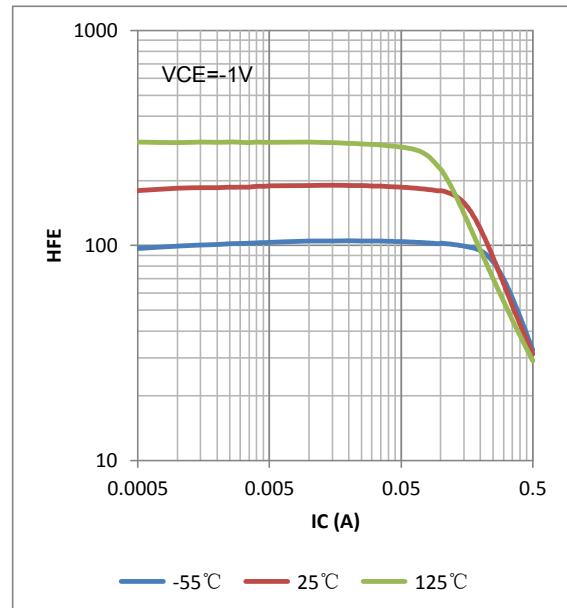
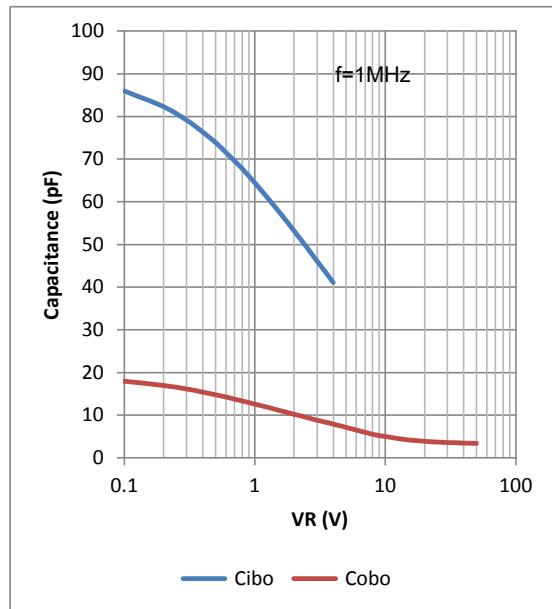


FIG.4 Collector Emitter Saturation Voltage vs. Collector Current

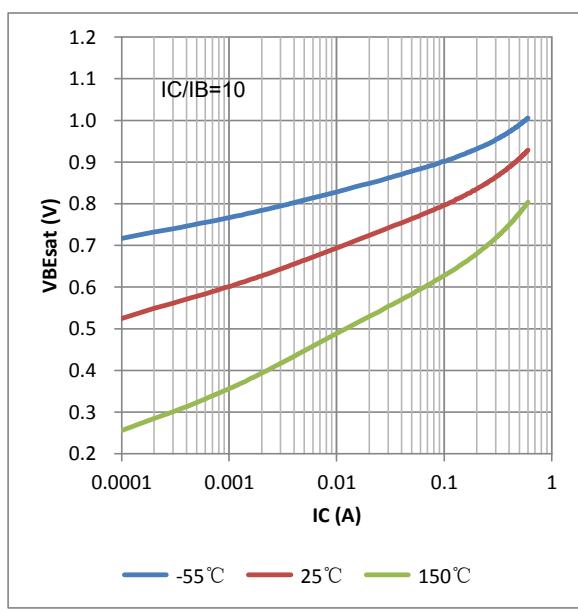


FIG.5 Base Emitter Saturation Voltage vs. Collector Current

## **LMBTA56LT1G,S-LMBTA56LT1G**

### **ELRCTRICAL CHARACTERISTICS CURVES**

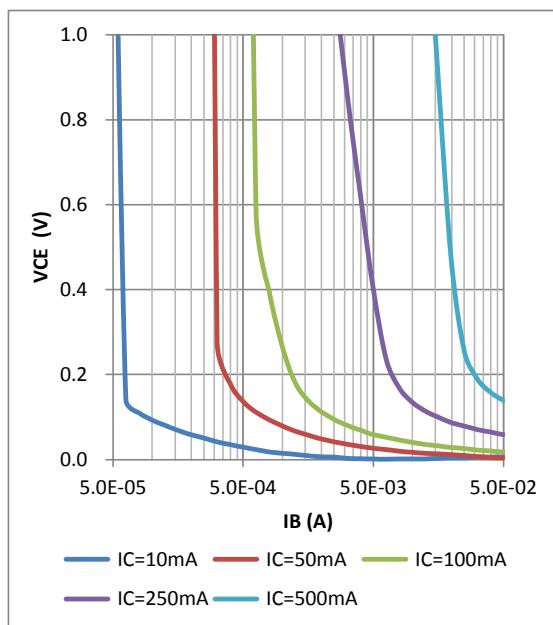


FIG.6 Collector Saturation Region

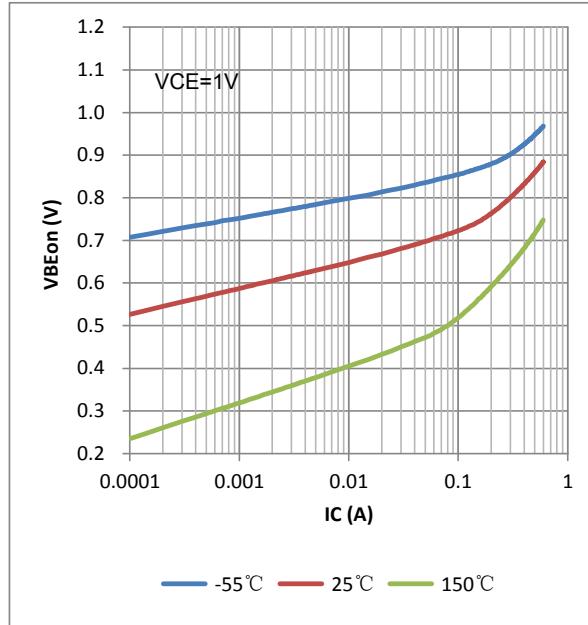
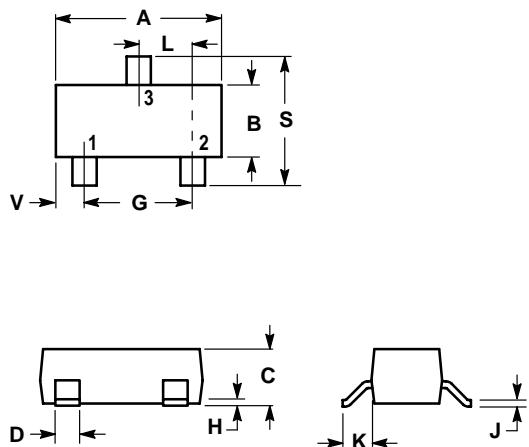


FIG.7 Base Emitter Voltage vs. Collector Current

# **LMBTA56LT1G,S-LMBTA56LT1G**

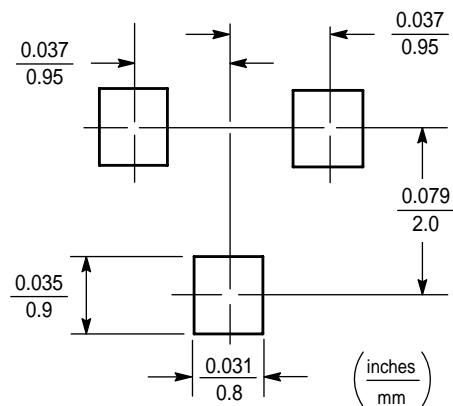
**SOT-23**



**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M,1982
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60



# X-ON Electronics

Largest Supplier of Electrical and Electronic Components

***Click to view similar products for Bipolar Transistors - BJT category:***

***Click to view products by Leshan manufacturer:***

Other Similar products are found below :

[619691C](#) [MCH4017-TL-H](#) [MMBT-2369-TR](#) [BC546/116](#) [BC557/116](#) [BSW67A](#) [NJVMJD148T4G](#) [NTE123AP-10](#) [NTE153MCP](#) [NTE16](#)  
[NTE195A](#) [NTE92](#) [C4460](#) [2N4401-A](#) [2N6728](#) [2SA1419T-TD-H](#) [2SA2126-E](#) [2SB1204S-TL-E](#) [2SC2712S-GR,LF](#) [2SC5488A-TL-H](#)  
[2SD2150T100R](#) [SP000011176](#) [2N2907A](#) [2N3904-NS](#) [2N5769](#) [2SC2412KT146S](#) [2SD1816S-TL-E](#) [CPH6501-TL-E](#) [MCH4021-TL-E](#)  
[MJE340](#) [US6T6TR](#) [NJK0281DG](#) [732314D](#) [CPH3121-TL-E](#) [CPH6021-TL-H](#) [873787E](#) [IMZ2AT108](#) [UMX21NTR](#) [MCH6102-TL-E](#)  
[NJK0302DG](#) [2N3583](#) [30A02MH-TL-E](#) [NSV40301MZ4T1G](#) [NTE13](#) [NTE26](#) [NTE282](#) [NTE323](#) [NTE350](#) [NTE81](#) [STX83003-AP](#)